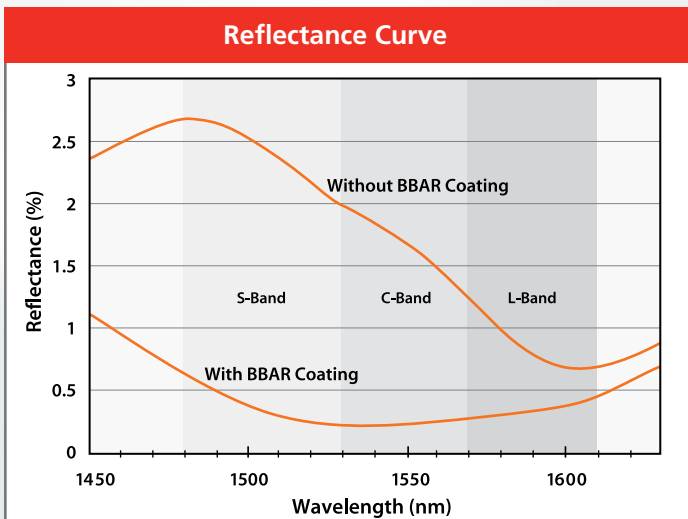
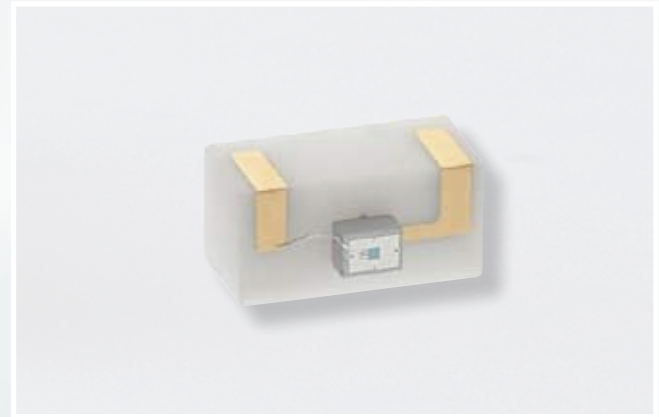


FCI-InGaAs-WCER-LR

Broadband Anti-Reflection Coated InGaAs Photodiodes

OSI Optoelectronics's latest product line includes a very low reflectance photodiode. Designed for telecommunication applications, the InGaAs/InP photodiode has a typical optical reflectance of less than .6% from 1520nm to 1620nm. This ultra low reflectance over the wide wavelength range was achieved by depositing a proprietary multi-layered Anti-Reflection coating directly onto the surface of the InGaAs/InP photodiode.



APPLICATIONS

- Wavelength Locker / Wavelength Monitoring
- Lasers Back Facet Monitoring
- DWDM
- Instrumentation

FEATURES

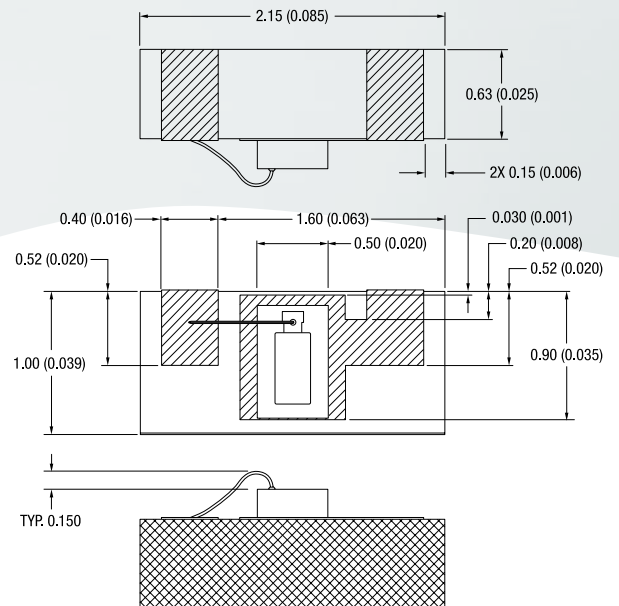
- Reflectance Less than 0.6%
- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm

Absolute Maximum Ratings

PARAMETERS	SYMBOL	MIN	MAX	UNITS
Storage Temperature	T_{stg}	-40	+85	$^{\circ}\text{C}$
Operating Temperature	T_{op}	0	+70	$^{\circ}\text{C}$
Soldering Temperature	T_{sld}	---	+260	$^{\circ}\text{C}$

Electro-Optical Characteristics $T_A = 23^{\circ}\text{C}$

PARAMETERS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	AA	---	---	250X500	---	$\mu\text{m} \times \mu\text{m}$
Responsivity	R_{λ}	$\lambda = 1310\text{nm}$	0.85	0.90	---	A/W
		$\lambda = 1550\text{nm}$	0.90	0.95	---	
Capacitance	C_j	$V_R = 5.0\text{V}$	---	15	---	pF
Dark Current	I_d	$V_R = 5.0\text{V}$	---	---	1	nA
Max. Reverse Voltage	---	---	---	---	20	V
Max. Reverse Current	---	---	---	---	2	mA
Max. Forward Current	---	---	---	---	5	mA
Reflectance	---	$1520\text{nm} \leq \lambda \leq 1620\text{nm}$	---	0.5	0.6	%



Notes:

- All units in millimeters.
- All devices are mounted with low out gassing conductive epoxy with tolerance of $\pm 25\mu\text{m}$. Eutectic mounting is also available upon request.